	Application No.	Applicant(s)
	10/675,829	NAGATOMO, MASAHIKO
Notice of Allowability	Examiner	Art Unit
	David Lam	2818
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.		
1. This communication is responsive to		
2. The allowed claim(s) is/are <u>1-5</u> .		
3. The drawings filed on <u>01 October 2003</u> are accepted by the Examiner.		
4.		
 Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/O Paper No./Mail Date 1/04 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material 	6. ☐ Interview Summary Paper No./Mail Dat 08), 7. ☐ Examiner's Amendr	

DAVID LAM
PRIMARY EXAMINER

Art Unit: 2818

Allowable Subject Matter

1. The following is an examiner's statement of reasons for allowance: Claims 1-5 are allowable over the prior art of record because none of the prior art whether taken singularly or in combination, especially when these limitations are considered within the specific combination claimed, to teach: a semiconductor memory device comprising: a voltage generator, among others as claimed in independent claim 1, having a second generator for generating a drain voltage to be applied to a drain line regardless of inputting of an enable signal; voltage generator, among others as claimed in independent claim 3, having a feedback stop circuit for temporarily stopping a feedback of an output voltage to increase the drain voltage when the enable signal is supplied thereto; memory array, among others as claimed in independent claim 4, has switching circuit for subjecting the drain voltage to be applied from the voltage generator to on-off control in respond to a selection signal; a voltage generator, among others as claimed in independent claim 5, which is provided for every plurality of memory arrays, and wherein the memory array is selected, the voltage generator corresponding to the selected memory array generates the drain voltage and applied to the selected memory array.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

- 2. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.
- Shokouhi et al. (6,233,177) disclose a bit line latch switching circuit for floating gate memory device requiring zero programming voltage.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to David Lam whose telephone number is 571-272-1782. The examiner can normally be reached on 6:00-4:30.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on 571-272-1787. The fax phone numbers for the organization where this application or proceeding is assigned is (703) 872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

D. Lam

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November 15, 2004